

UNISONIC TECHNOLOGIES CO., LTD

BC847BS

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

NPN GENERAL PURPOSE **AMPLIFIER**

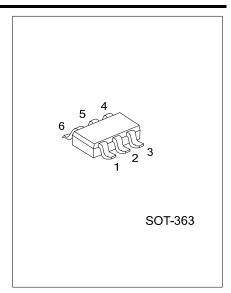
DESCRIPTION

The UTC BC847BS is a dual NPN transistors; it uses UTC's advanced technology to provide customers high DC current gain, low power dissipation and low collector-emitter saturation voltage.

The UTC BC847BS is suitable for a high gain, low noise and general purpose amplifier.

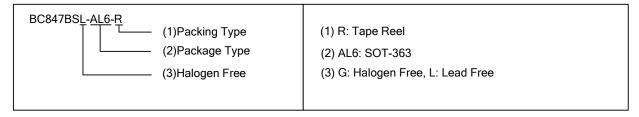
FEATURES

- * Low saturation voltage
- * High DC current gain

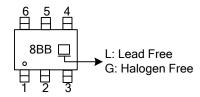


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment						Doolsing
Lead Free	Halogen Free	Package	1	2	3	4	5	6	Packing
BC847BSL-AL6-R	BC847BSG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel



MARKING



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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Base Voltage	V _{CES}	50	V	
Collector-Emitter Voltage	V_{CEO}	45	V	
Emitter-Base Voltage	V_{EBO}	6.0	V	
Continuous Collector Current	Ic	100	mA	
Power Dissipation		325	mW	
Derate above 25°C	P _D	2.8	mW/°C	
Junction Temperature	TJ	-55~+150	°C	
Storage Temperature Range	T _{STG}	-55~+150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL DATA** (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	357	°C/W	

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CES}	I _C =10μA, I _E =0	50			V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C =10mA, I _B =0	45			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =10μA, I _C =0	6.0			V
Callagton Cut Off Cumant	I _{CBO}	V _{CB} =30V			15	nA
Collector Cut-Off Current		V _{CB} =30V, T _A =150°C			5.0	μΑ
Callantar Freitter Caturation Valtage	V	I _C =10mA, I _B =0.5mA			0.25	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =5.0mA			0.6	V
Daga Fraitter Turn On Voltage	.,	I _C =2.0mA, V _{CE} =5.0V	0.58		0.70	V
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	I _C =10mA, V _{CE} =5.0V			0.77	V
DC Current Gain	h _{FE}	I _C =2.0mA, V _{CE} =5.0V	200		450	
Transition Frequency	f _T	I _C =10mA, V _{CE} =5.0V, f=100MHz	100			MHz
Output Capacitance	C _{obo}	V _{CB} =10V, f=1.0MHz			4.5	pF
Noise Figure	NF	I_{C} =0.2mA, V_{CE} =5.0V, R_{S} =2.0k Ω , f=1.0kHz, BW=200Hz			10	dB

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